

深圳市诚芯微科技股份有限公司

SHENZHEN CHENGXINWEI TECHNOLOGY CO., LTD.

N-MOSFET 60V, $8m\Omega$, 56A

CX60R10G

Features

- Extremely low on-resistance R_{DS(on)}
- Excellent Q_qxR_{DS(on)} product(FOM)
- Qualified according to JEDEC criteria

Product Summary

V_{DS}	60V
R _{DS(on) typ.}	8mΩ
I_D	56A

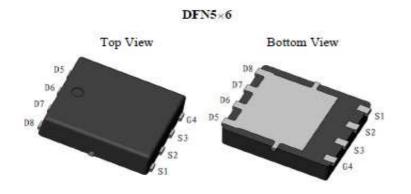
100% DVDS Tested

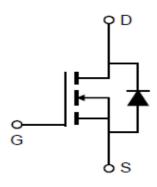
Applications

- · Motor control and drive
- Battery management
- UPS (Uninterrupible Power Supplies)



100% Avalanche Tested





Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	60	V
Continuous drain current			
T _C = 25°C (Silicon limit)	I_{D}	56	А
T _C = 25°C (Package limit)		124	
T _C = 100°C (Silicon limit)		36	
Pulsed drain current ($T_C = 25$ °C, t_p limited by T_{jmax})	${ m I}_{ m D\ pulse}$	224	Α
Avalanche energy, single pulse (L=0.5mH, Rg=25 Ω)	E _{AS}	60	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation ($T_C = 25^{\circ}C$)	P _{tot}	61	W
Operating junction and storage temperature	T_{j} , T_{stg}	-55+150	°C
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T _{sold}	260	°C